Electrical Characteristics of the IGBT T_j= 25 unless otherwise specified

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Collector-Emitter Breakdown Voltage	BV_{CES}	V_{GE}=0V, I_C	650		-	V
Gate Threshold Voltage	$V_{GE(th)}$	V_{GE}=V_{CE}, I_C=1mA	4.4	5.2	6.0	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$					

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Electrical Characteristics of the Diode T_j= 25 unless otherwise specified

Electrical Characteristics of the DIODE

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at T_j= 25						
Reverse Recovery Current	I_{rr}	I_F=10A, V_R=300V, -di/dt= 365	-	6	-	A
Diode reverse recovery time	trr		-	176	-	ns
Reverse Recovery Charge	Q_{rr}		-	0.12	-	uC
Reverse Recovery Energy	40eg		-	0.05	-	mJ
Dynamic , at Tj= 125						
Reverse Recovery Current	I_{rr}					

I_F=10A,

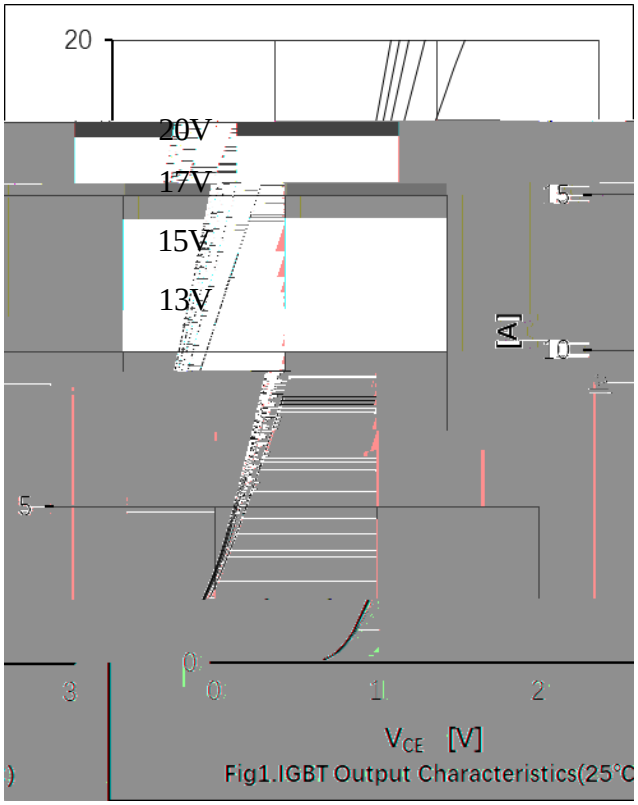


Fig1.IGBT Output Characteristics(25°C

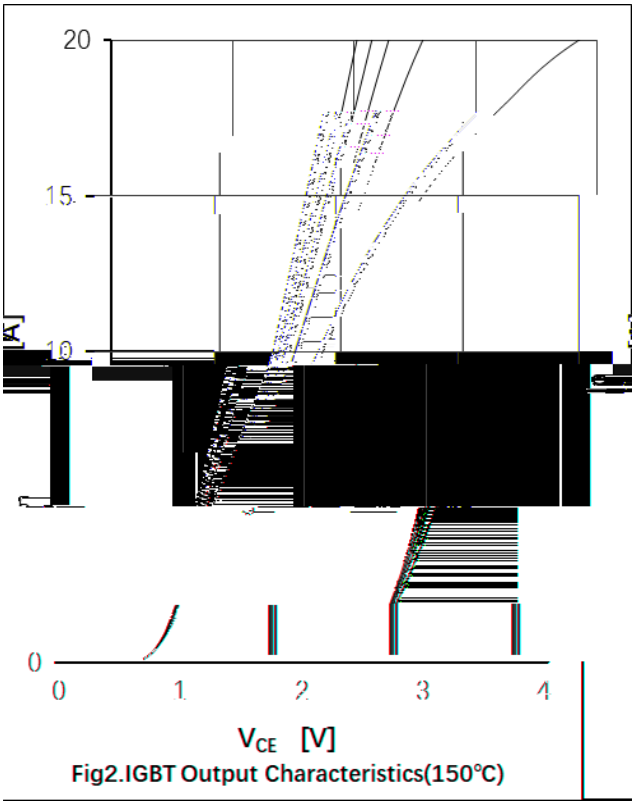


Fig2.IGBT Output Characteristics(150°C)

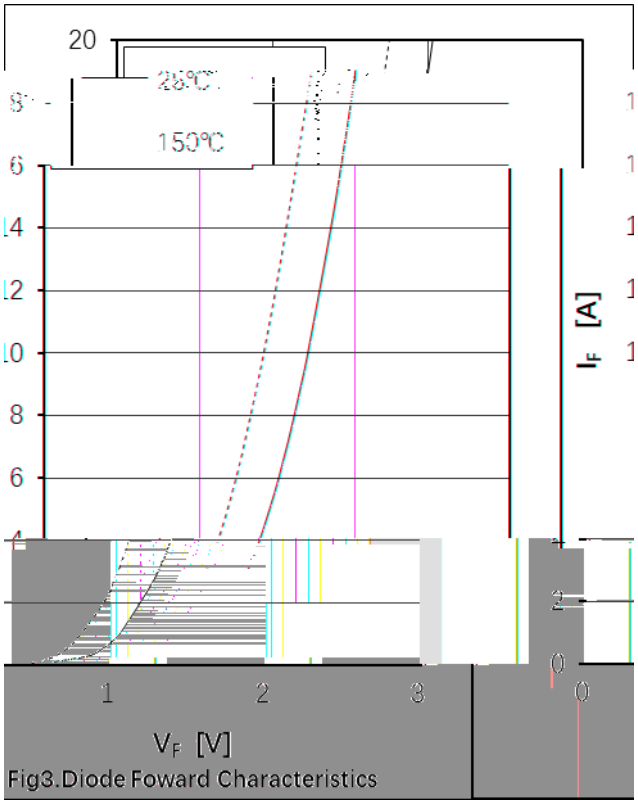


Fig3.Diode Foward Characteristics

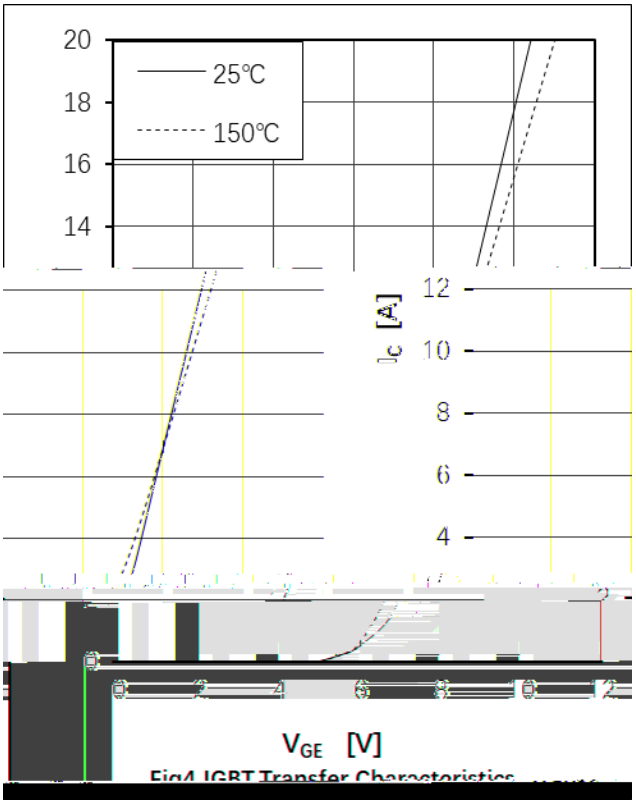
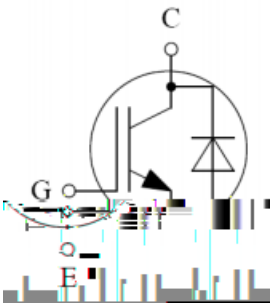


Fig4.IGBT Transfer Characteristics



Package Outline Information

CASE: TO-220F package information

SYMBOL	单位：mm			SYMBOL	单位：mm			SYMBOL	单位：mm		
	MIN.	NOM.	MAX.		MIN.	NOM.	MAX.		MIN.	NOM.	MAX.
A	4.40	4.50	4.60	L	10.00	10.16	10.30	Q1	3.30	3.40	3.50
A1	2.34	2.54	2.74	L1	9.04	12.06	12.22	Q	3.10	3.20	3.30
Φ	45°	48°	A2	2.66	2.76	2.86	L2	9.40	9.50	9.60	Q2
A3		1.08REF			L3	1.40	1.50	1.60			
b1	1.18	1.20	1.24	R1	15.80	15.90	16.00				
b2	0.75	0.80	0.85	R2	3.20	3.30	3.40				
b3	1.70	1.90	2.10	R3	6.00	7.60	7.70				
c	0.46	0.50	0.63	R4	0.60	0.70	0.80				
D	15.67	15.87	16.07	L	12.76	12.96	13.16				
D1	9.64	9.80	9.80	L1	2.92	3.07	3.22				
e	2.50	2.54	2.58	Q	3.08	3.18	3.28				
e1	5.08REF			ΦP	3.08	3.18	3.28				